

## E. Compound Semiconductors 분과

Room E

창의관 (B113)

일 시 : 2월 17일(금) 09:30-11:00

세션명 : [FE1-E] Electronics Devices and Processes I

좌 장 : 윤형섭(ERTI), 곽준섭(순천대학교)

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- FE1-E-1 09:30-10:00 **[Invited] Next Generation Power Semiconductor Devices**  
저자: 차호영  
소속: 홍익대학교 전자전기공학부
- FE1-E-2 10:00-10:15 **다중 Al<sub>2</sub>O<sub>3</sub>/Ga<sub>2</sub>O<sub>3</sub> 스택을 이용한 고전압 AlGaN/GaN HEMTs**  
저자: 안우진, 석오균, 김영실, 한민구  
소속: 서울대학교 전기공학부
- FE1-E-3 10:15-10:30 **The Effects of Interface Plasma Passivation on Pt/Al<sub>2</sub>O<sub>3</sub>/6H-SiC MOS Devices**  
저자: Seung-Chan Heo<sup>1</sup>, Dongjun Yoo<sup>1</sup>, Tae Yong Park<sup>1</sup>, Hyeongtag Jeon<sup>1</sup>, Tae Young Jang<sup>2</sup>, Rino Choi<sup>2</sup>, and Changhwan Choi<sup>1</sup>  
소속: <sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>School of Materials Science and Engineering, Inha University
- FE1-E-4 10:30-10:45 **Effect of Al<sub>2</sub>O<sub>3</sub> Gate Insulator Thickness on Characteristics of Normally-off GaN MOSFETs**  
저자: Sung-Dal Jung<sup>1</sup>, Ki-Won Kim<sup>1</sup>, Mi-Kyung Kwon<sup>1</sup>, Dong-Seok Kim<sup>1</sup>, Hee-Sung Kang<sup>1</sup>, Ki-Sik Im<sup>1</sup>, Chul-Ho Won<sup>1</sup>, Chan-Ho Bu<sup>1</sup>, Ryun-Hwi Kim<sup>2</sup>, Kyu-Il Jang<sup>1</sup>, Chung-Mo Yang<sup>1</sup>, and Jung-Hee Lee<sup>1</sup>  
소속: <sup>1</sup>School of Electrical Engineering & Computer Science, Kyungpook National University, <sup>2</sup>Department of Sensor & Display Engineering, Kyungpook National University
- FE1-E-5 10:45-11:00 **Packaged GaN HEMT Power Bar with 17 W Output Power at 3 GHz**  
저자: 장우진, 임종원, 주철원, 강동민, 이상흥, 김성일, 안호균, 윤형섭, 민병규, 김해천, 문재경, 남은수

소속: 한국전자통신연구원 RF융합부품연구팀